



No.2261A

2SA1562

PNP Epitaxial Planar Silicon Transistor

High-h<sub>FE</sub>, AF Amp Applications

**Applications**

- . AF amp, various drivers

**Features**

- . Adoption of MBIT process
- . High DC current gain
- . Large current capacity
- . Low collector to emitter saturation voltage
- . High V<sub>EBO</sub>

**Absolute Maximum Ratings at Ta=25°C**

			unit
Collector to Base Voltage	V <sub>CBO</sub>	-30	V
Collector to Emitter Voltage	V <sub>CEO</sub>	-25	V
Emitter to Base Voltage	V <sub>EBO</sub>	-15	V
Collector Current	I <sub>C</sub>	-1.2	A
Collector Current(Pulse)	I <sub>CP</sub>	-2	A
Collector Dissipation	P <sub>C</sub>	1	W
		15	W
Junction Temperature	T <sub>J</sub>	150	°C
Storage Temperature	T <sub>stg</sub>	-55 to +150	°C

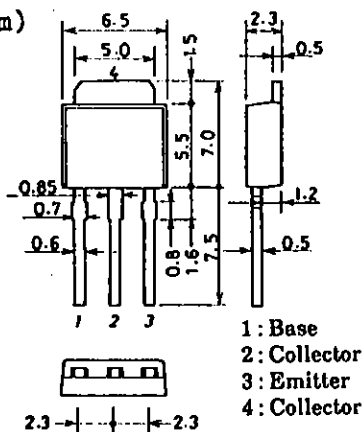
**Electrical Characteristics at Ta=25°C**

			min	typ	max	unit
Collector Cutoff Current	I <sub>CBO</sub>	V <sub>CB</sub> =-20V, I <sub>E</sub> =0			-1	µA
Emitter Cutoff Current	I <sub>EBO</sub>	V <sub>EB</sub> =-10V, I <sub>C</sub> =0			-1	µA
DC Current Gain	h <sub>FE</sub> (1)	V <sub>CE</sub> =-5V, I <sub>C</sub> =-100mA	500	800	1200	
	h <sub>FE</sub> (2)	V <sub>CE</sub> =-5V, I <sub>C</sub> =-10mA	350			
Gain-Bandwidth Product	f <sub>T</sub>	V <sub>CE</sub> =-10V, I <sub>C</sub> =-50mA		130		MHz
Output Capacitance	c <sub>ob</sub>	V <sub>CB</sub> =-10V, f=1MHz		40		pF
C-E Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =-500mA, I <sub>B</sub> =-10mA	-0.1	-0.5		V
B-E Saturation Voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> =-500mA, I <sub>B</sub> =-10mA	-0.78	-1.1		V

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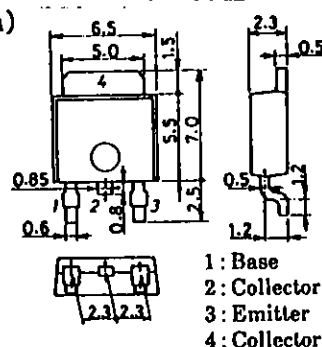
**Package Dimensions 2045B**

(unit:mm)



**Package Dimensions 2044B**

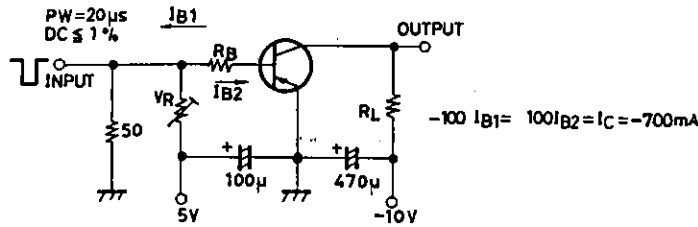
(unit:mm)



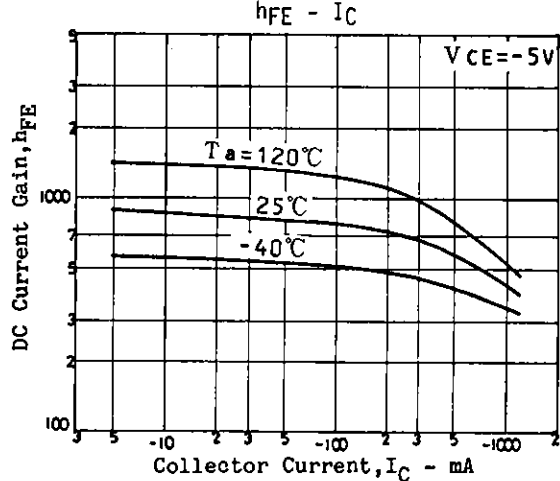
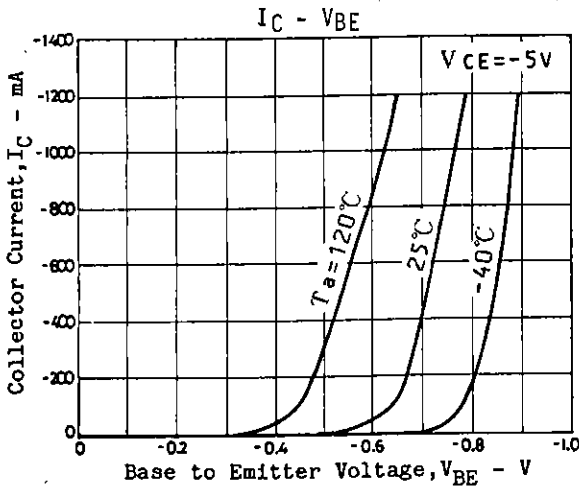
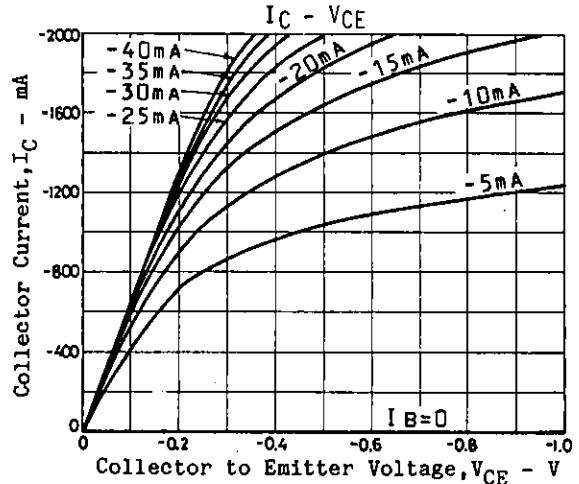
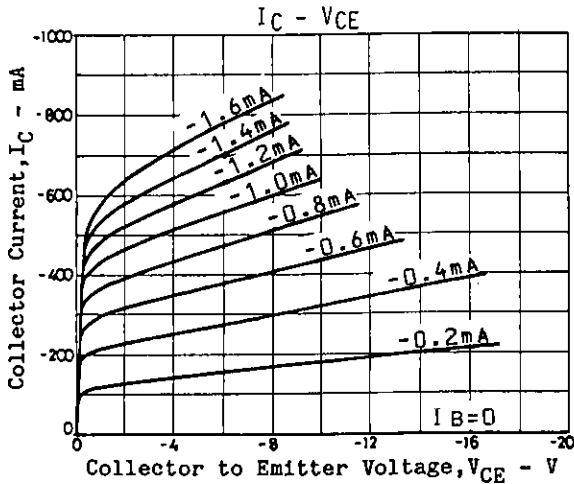
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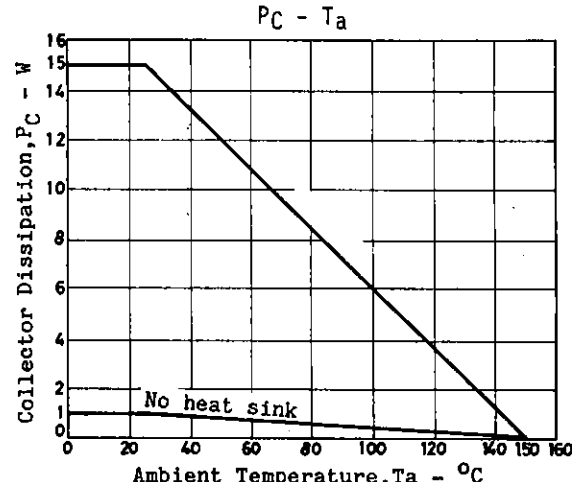
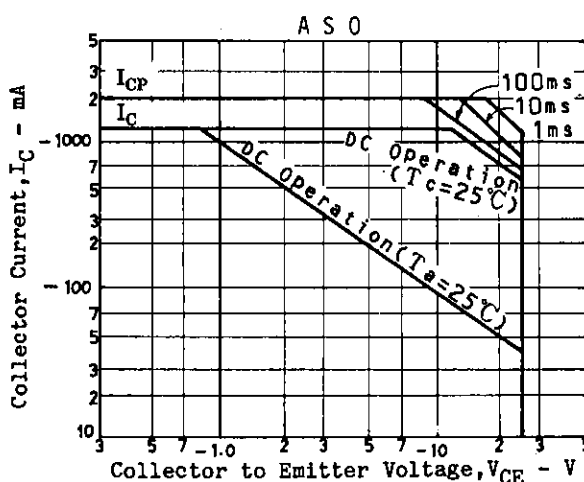
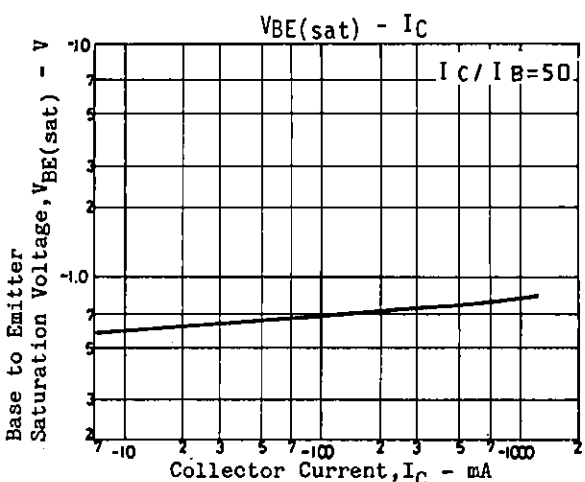
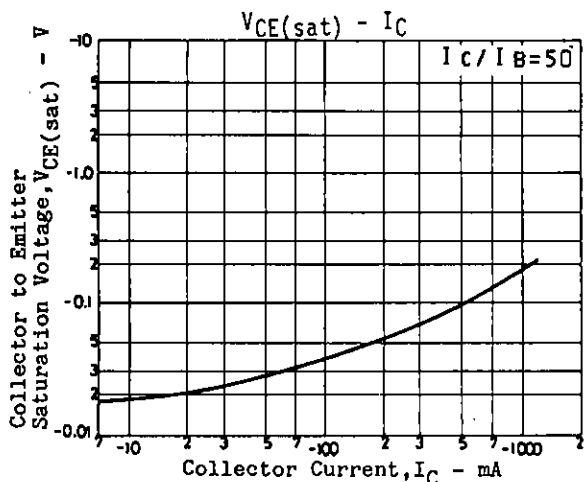
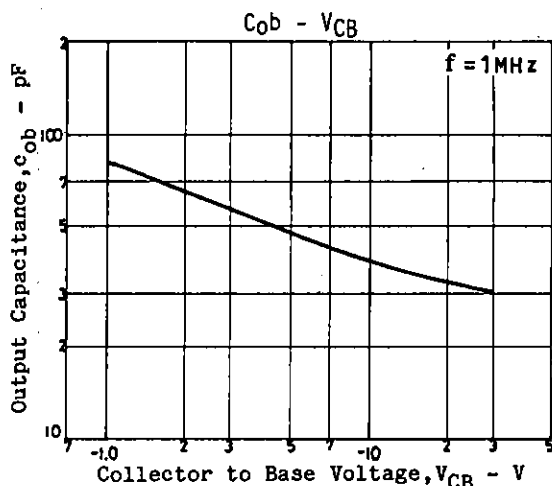
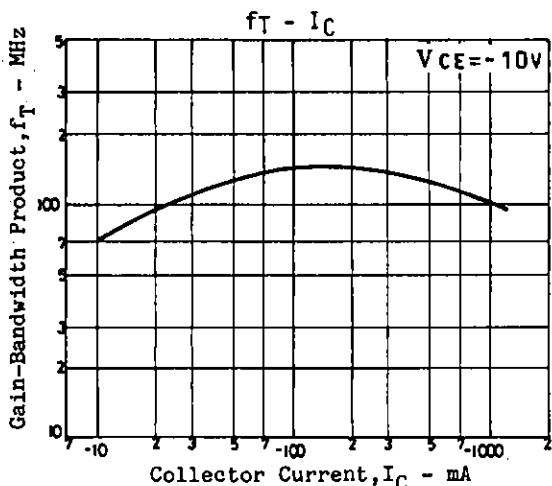
			min	typ	max	unit
C-B Breakdown Voltage	$V_{(BR)CBO}$	$I_C = (-) 10\mu A, I_E = 0$	-30			V
C-E Breakdown Voltage	$V_{(BR)CEO}$	$I_C = -1mA, R_{BE} = \infty$	-25			V
E-B Breakdown Voltage	$V_{(BR)EBO}$	$I_E = -10\mu A, I_C = 0$	-15			V
Turn-ON Time	$t_{on}$	See specified Test Circuit.	0.31			$\mu s$
Storage Time	$t_{stg}$	"	0.88			$\mu s$
Fall Time	$t_f$	"	0.23			$\mu s$

Switching Time Test Circuit



Unit (Resistance :  $\Omega$ , Capacitance : F)





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